



Description

JMT N And P-Channel Enhancement Mode MOSFET

Features

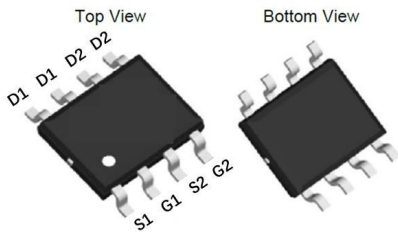
- N-Channel: 40V, 10A
 $R_{DS(ON)} < 20m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 27m\Omega @ V_{GS} = 4.5V$
- P-Channel: -40V, -10A
 $R_{DS(ON)} < 44m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 62m\Omega @ V_{GS} = -4.5V$
- Excellent Gate Charge x $R_{DS(ON)}$ Product(FOM)
- Very Low On-resistance $R_{DS(ON)}$
- Fast Switching Speed

Application

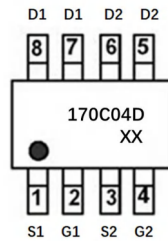
- Battery Protection
- Load Switch
- Power Management



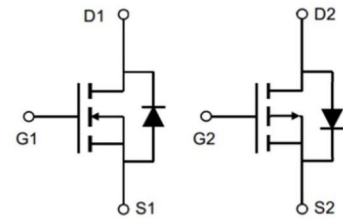
100% UIS TESTED!
100% ΔVds TESTED!



SOP-8



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
170C04D	JMTP170C04D	TAPING	SOP-8	13inch	4000	48000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max. N-Channel	Max. P-Channel	Units
V_{DSS}	Drain-Source Voltage	40	-40	V
V_{GSS}	Gate-Source Voltage	± 20	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	-10	A
		$T_A = 100^\circ C$	-6.5	A
I_{DM}	Pulsed Drain Current ^{note1}	40	-40	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	19	27.5	mJ
P_D	Power Dissipation	$T_A = 25^\circ C$	7.5	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	36.8	16.7	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ C$



N-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =10V, I _D =10A	-	15	20	mΩ
		V _{GS} =4.5V, I _D =5A	-	19	27	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1.0MHz	-	980	-	pF
C _{oss}	Output Capacitance		-	86.2	-	pF
C _{rss}	Reverse Transfer Capacitance		-	68.5	-	pF
Q _g	Total Gate Charge	V _{DS} =20V, I _D =5A, V _{GS} =10V	-	11	-	nC
Q _{gs}	Gate-Source Charge		-	1.9	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	2.2	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =20V, I _D = 5A, R _L =2.5Ω, R _{REN} =3Ω	-	11	-	ns
t _r	Turn-on Rise Time		-	13	-	ns
t _{d(off)}	Turn-off Delay Time		-	36	-	ns
t _f	Turn-off Fall Time		-	9	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	10	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	40	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = 10A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	T _J =25°C,	-	19	-	ns
Q _{rr}	Body Diode Reverse Recovery	I _F =10A, di/dt=100A/μs	-	11	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=8.7A

T_J=25°C, V_{DD}=-30V, V_G= -10V, L=0.5mH, R_g=25Ω, I_{AS}= -10.5A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



P-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -40V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} = -10V, I _D = -8A	-	34	44	mΩ
		V _{GS} = -4.5V, I _D = -5A	-	46	62	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -20V, V _{GS} =0V, f=1.0MHz	-	1034	-	pF
C _{oss}	Output Capacitance		-	107	-	pF
C _{rss}	Reverse Transfer Capacitance		-	79.5	-	pF
Q _g	Total Gate Charge	V _{DS} = -20V, I _D = -5A, V _{GS} = -10V	-	20	-	nC
Q _{gs}	Gate-Source Charge		-	3.5	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	4.2	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -20V, I _D = -5A, V _{GS} = -10V, R _{GEN} =2.5Ω	-	8	-	ns
t _r	Turn-on Rise Time		-	15	-	ns
t _{d(off)}	Turn-off Delay Time		-	23	-	ns
t _f	Turn-off Fall Time		-	9	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-10	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -10A	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	T _J =25°C,	-	29	-	ns
Q _{rr}	Reverse Recovery Charge	I _F =10A, dI/dt=100A/μs	-	20	-	nC



Typical Performance Characteristics-N

Figure 1: Output Characteristics

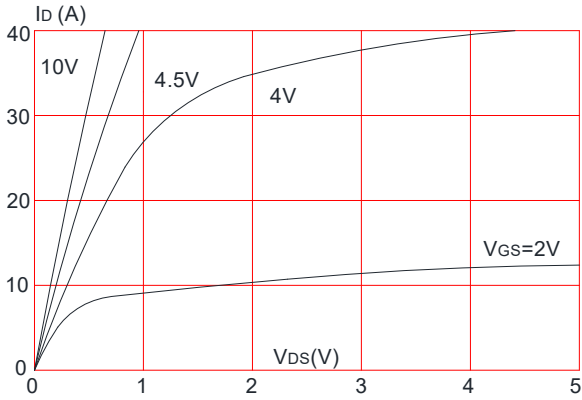


Figure 2: Typical Transfer Characteristics

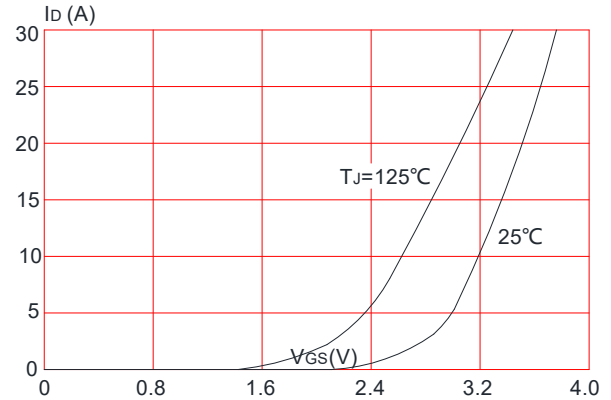


Figure 3: On-resistance vs. Drain Current

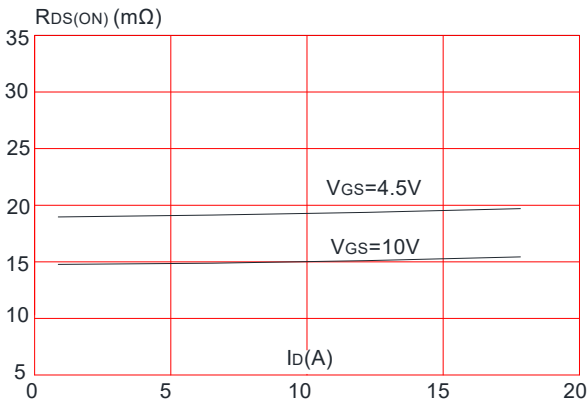


Figure 4: Body Diode Characteristics

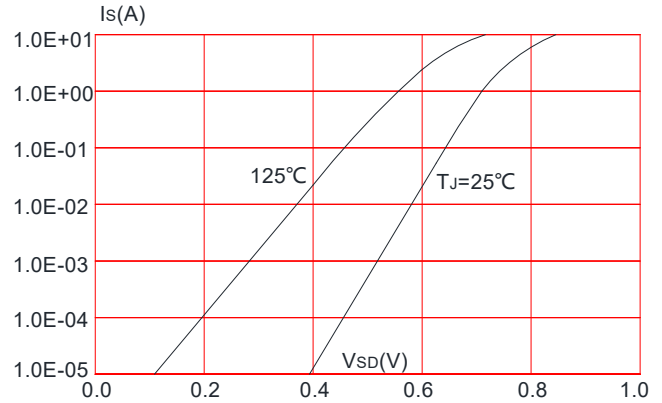


Figure 5: Gate Charge Characteristics

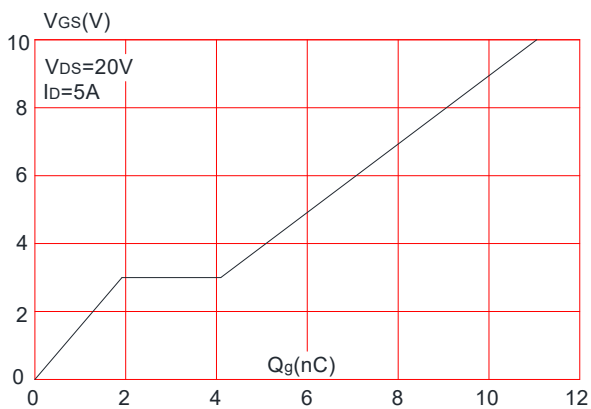


Figure 6: Capacitance Characteristics

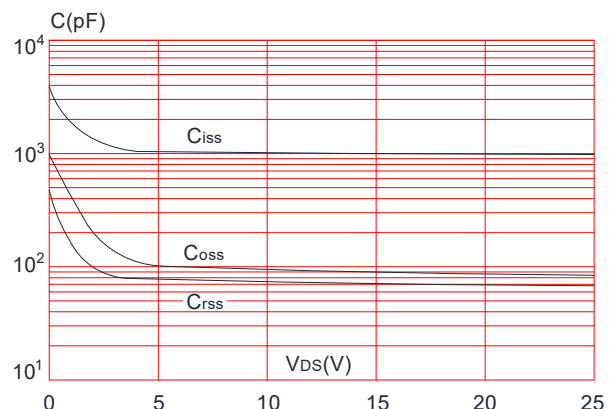




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

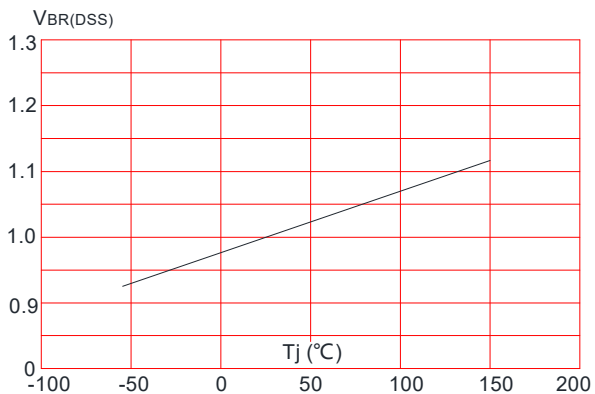


Figure 8: Normalized on Resistance vs. Junction Temperature

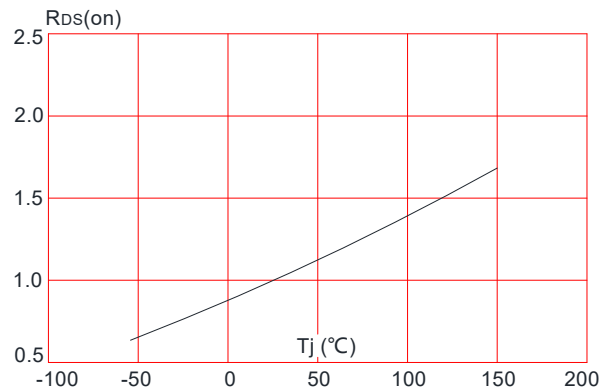


Figure 9: Maximum Safe Operating Area

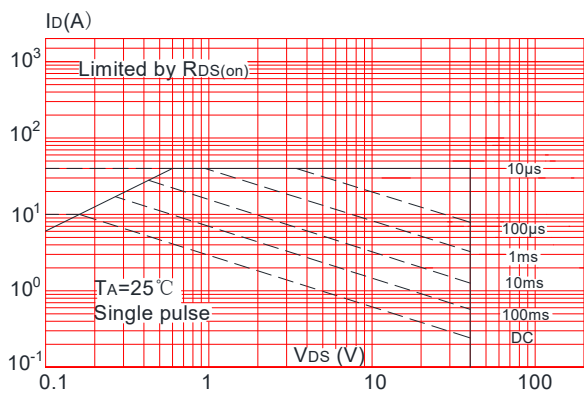


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

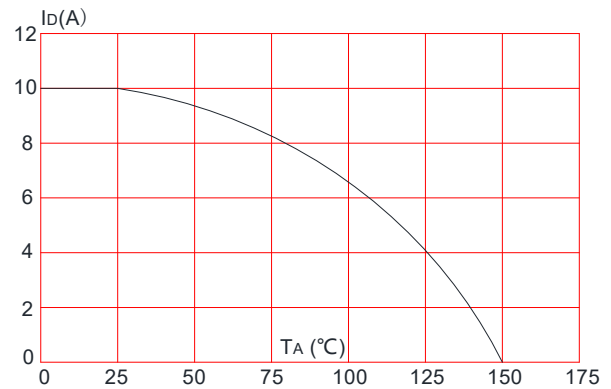
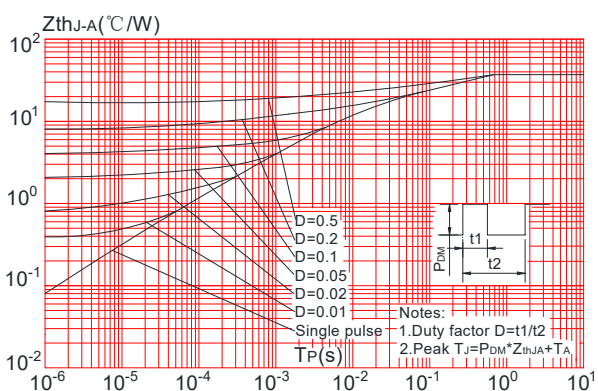


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit-N

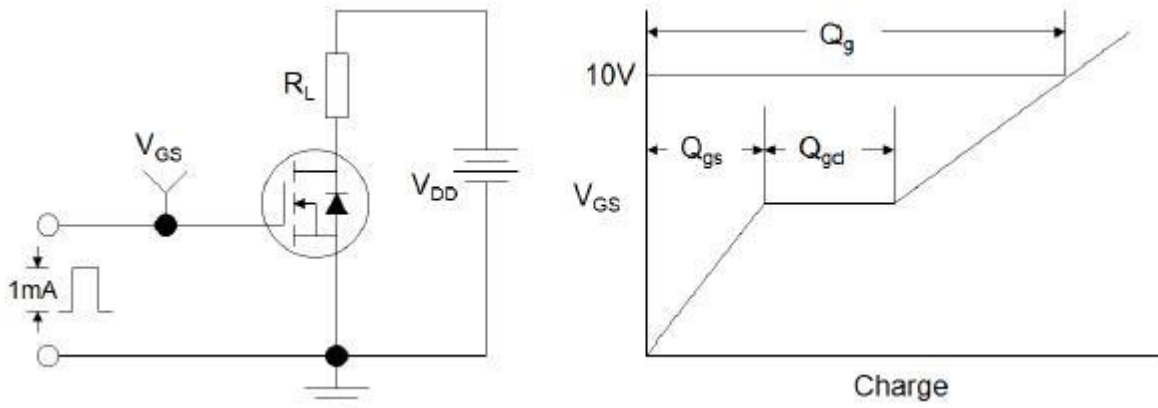


Figure1:Gate Charge Test Circuit & Waveform

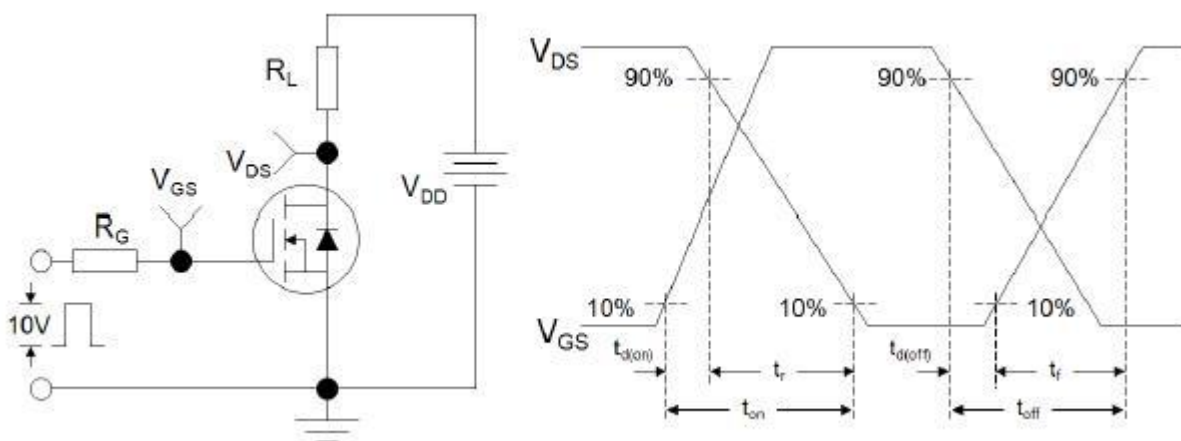


Figure 2: Resistive Switching Test Circuit & Waveforms

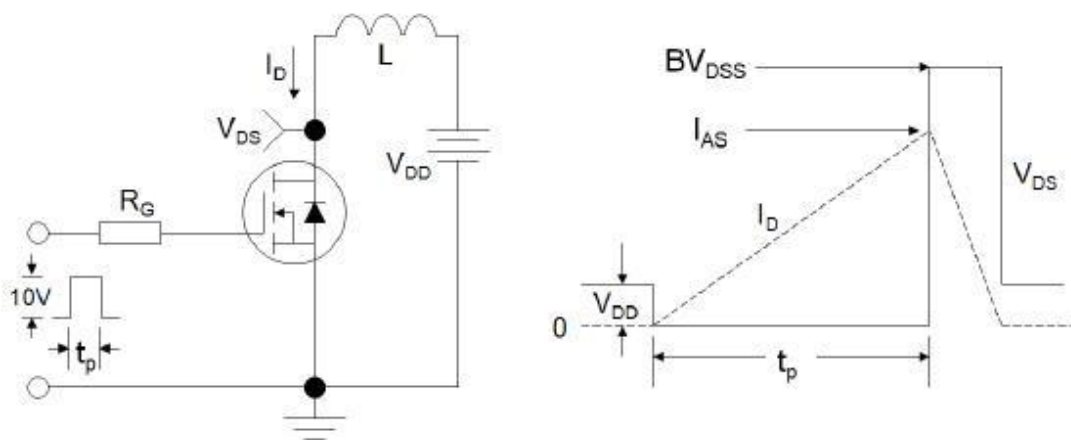


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



Typical Performance Characteristics-P

Figure 1: Output Characteristics

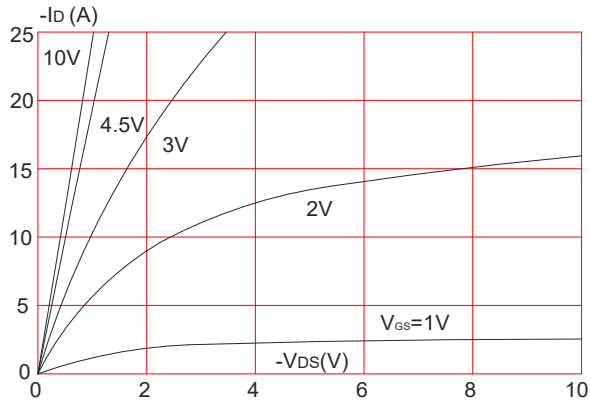


Figure 2: Typical Transfer Characteristics

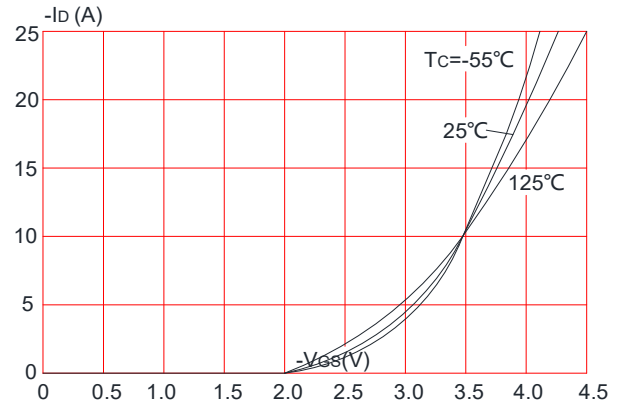


Figure 3: On-resistance vs. Drain Current

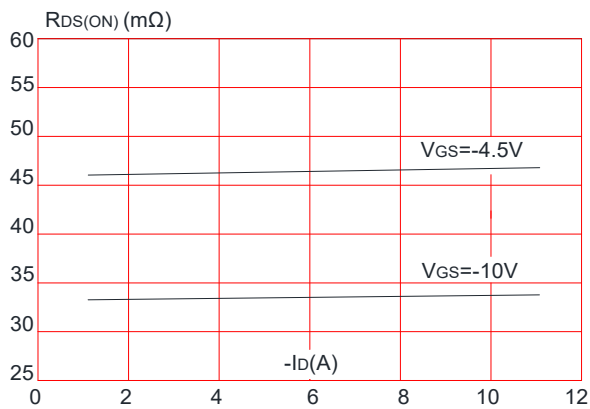


Figure 4: Body Diode Characteristics

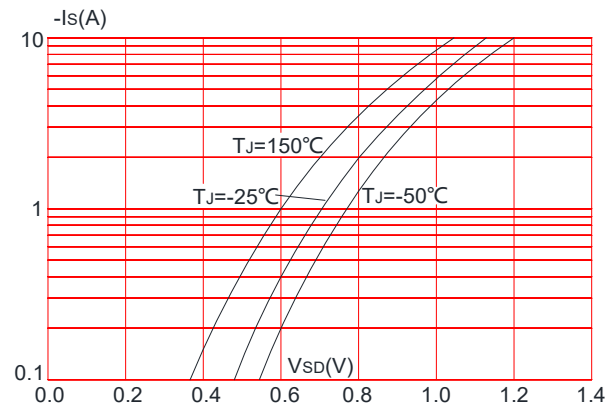


Figure 5: Gate Charge Characteristics

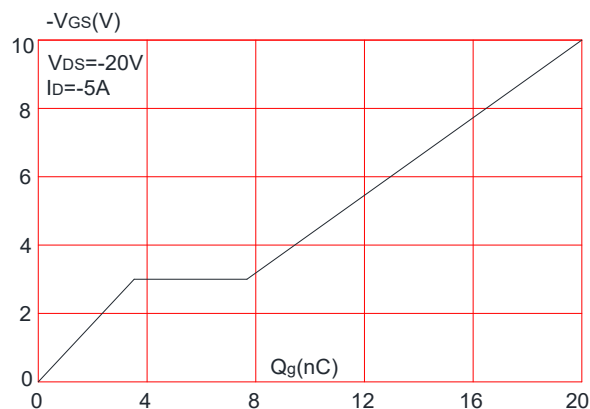


Figure 6: Capacitance Characteristics

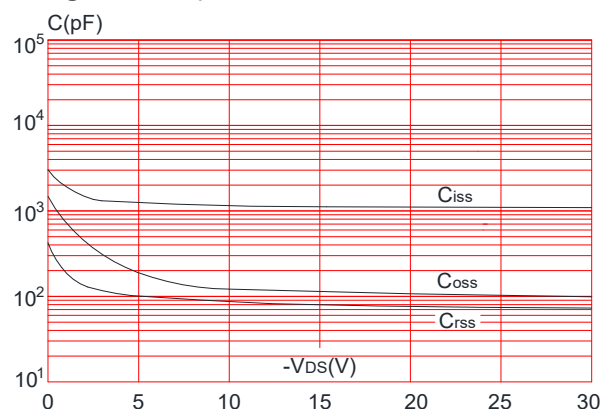




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

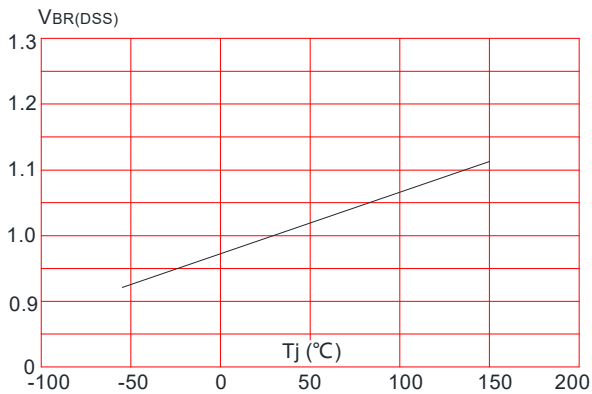


Figure 8: Normalized on Resistance vs. Junction Temperature

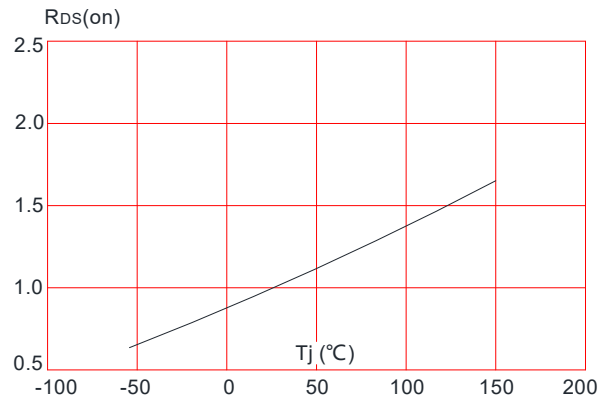


Figure 9: Maximum Safe Operating Area

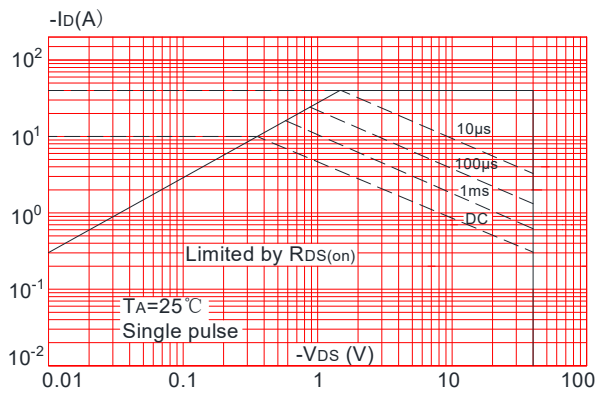


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

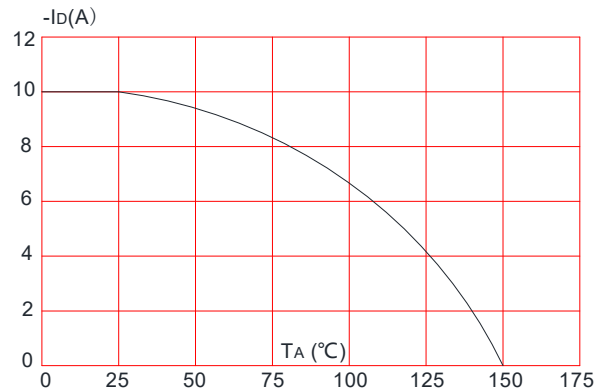
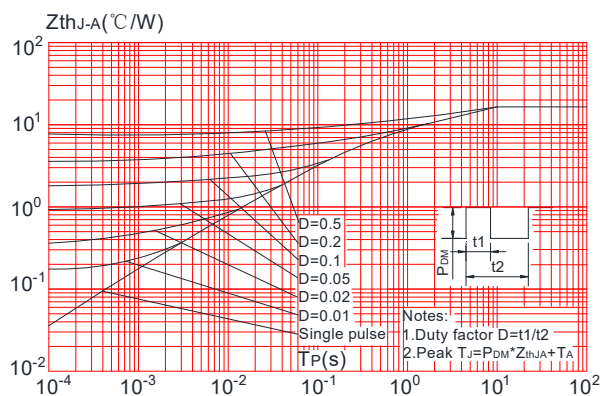
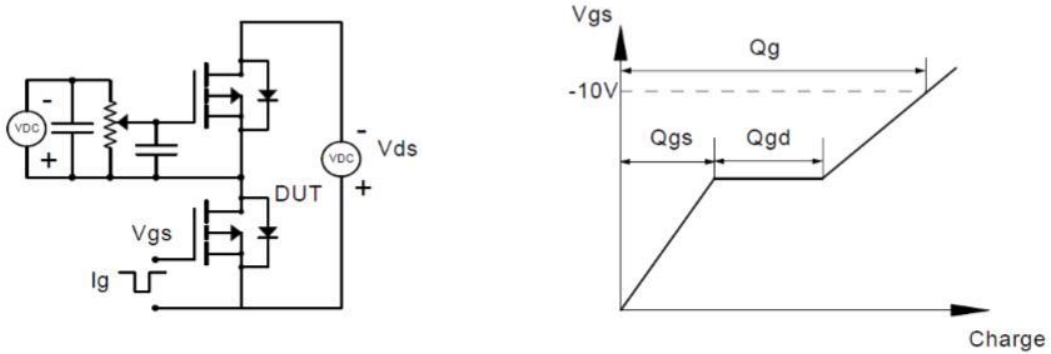


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

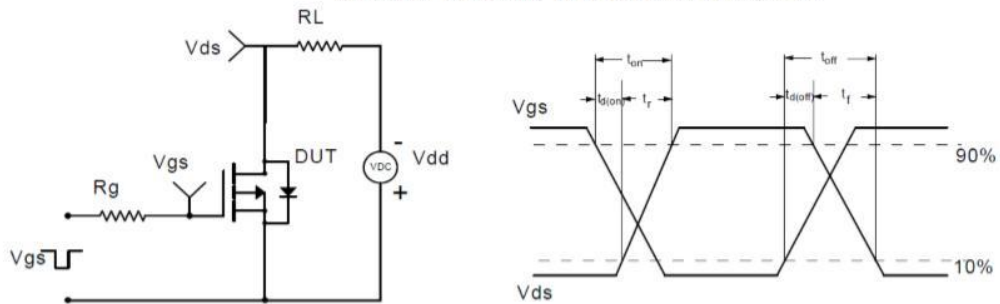


Test Circuit-P

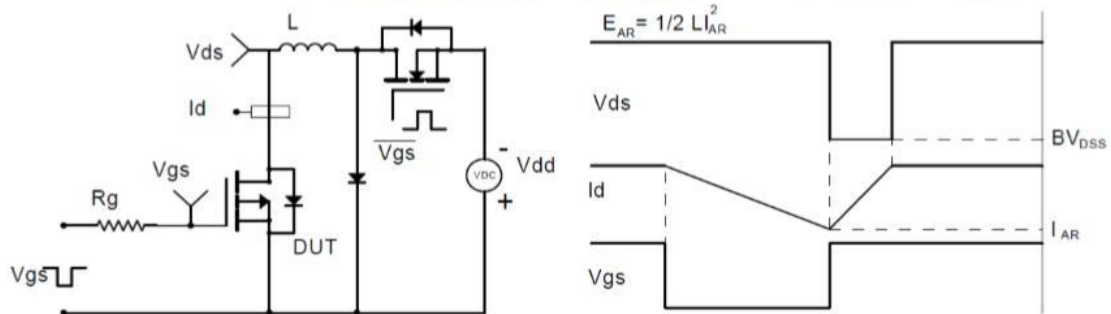
Gate Charge Test Circuit & Waveform



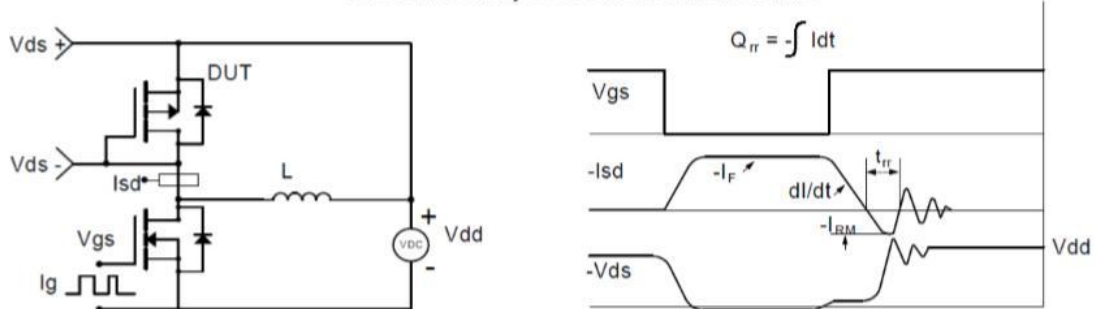
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

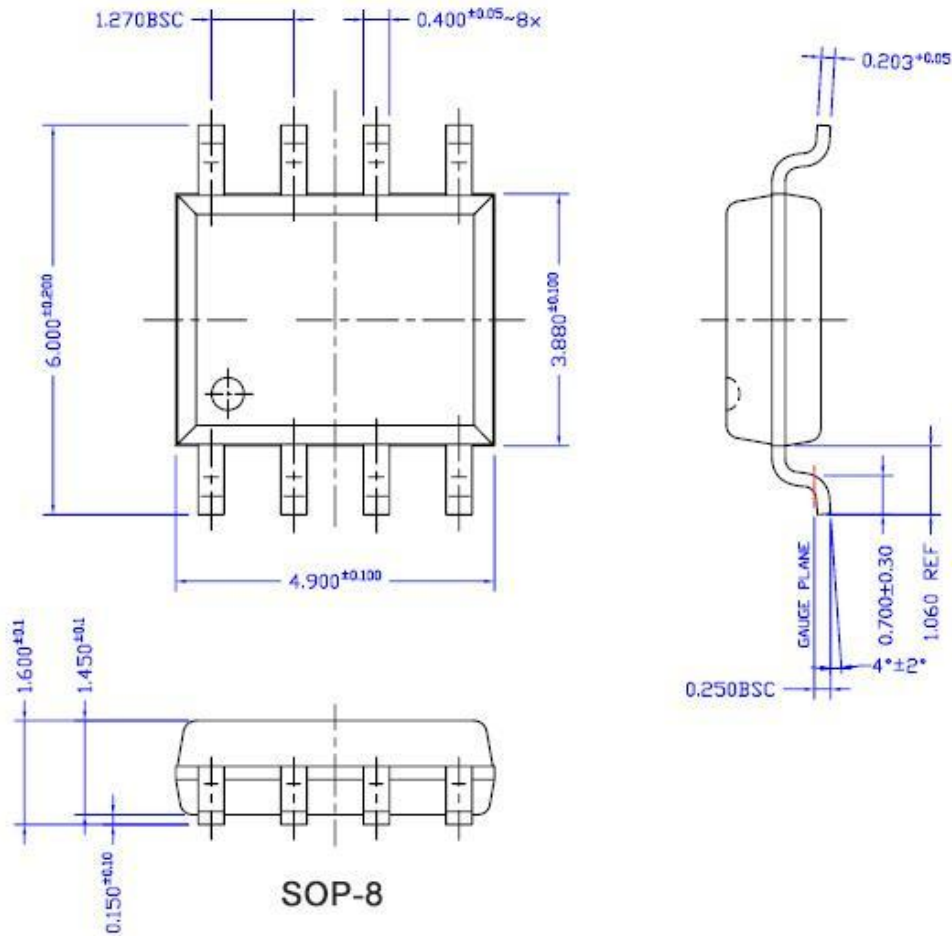


Diode Recovery Test Circuit & Waveforms





Package Mechanical Data-SOP-8



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